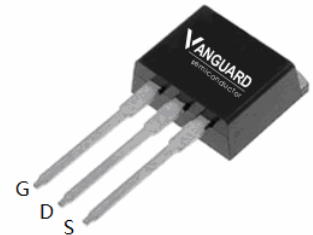


Features

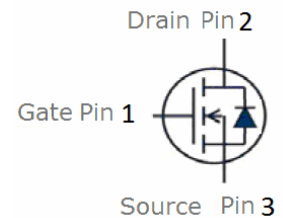
- N-Channel
- Enhancement mode
- Very low on-resistance $R_{DS(on)}$ @ $V_{GS}=4.5\text{ V}$
- Fast Switching
- 100% Avalanche Tested
- Pb-free lead plating; RoHS compliant



V_{DS}	100	V
$R_{DS(on),TYP}@ V_{GS}=4.5\text{ V}$	16.5	m Ω
I_D	42	A

TO-251-L


Part ID	Package Type	Marking	Tape and reel information
VS1H42AI	TO-251-L	1H42AI	75pcs/Tube



Maximum ratings, at $T_j=25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter	Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage	100	V
I_S	Diode continuous forward current	$T_C=25^\circ\text{C}$ 42	A
I_D	Continuous drain current @ $V_{GS}=10\text{V}$	$T_C=25^\circ\text{C}$ 42	A
		$T_A=100^\circ\text{C}$ 27	A
I_{DM}	Pulse drain current tested ①	$T_C=25^\circ\text{C}$ 168	A
EAS	Avalanche energy, single pulsed ②	$I_D=16\text{A}$ 64	mJ
IAS	Avalanche energy, single pulsed ②	20	A
P_D	Maximum power dissipation	$T_A=25^\circ\text{C}$ 71	W
V_{GS}	Gate-Source voltage	± 20	V
$T_{STG} T_J$	Storage and operating temperature range	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typical	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	2.1	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	72	$^\circ\text{C/W}$

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_c = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current(T _c =25°C)	V _{DS} =100V, V _{GS} =0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T _c =125°C)	V _{DS} =100V, V _{GS} =0V	--	--	100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	2.0	3.0	V
R _{DS(ON)}	Drain-Source On-State Resistance ^③	V _{GS} =10V, I _D =20A	--	14.0	18	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance ^③	V _{GS} =4.5V, I _D =5A	--	16.5	20	mΩ
Dynamic Electrical Characteristics @ T_c = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	--	4280	--	pF
C _{oss}	Output Capacitance		--	188	--	pF
C _{rss}	Reverse Transfer Capacitance		--	140	--	pF
Q _g	Total Gate Charge	V _{DS} =50V, I _D =4A, V _{GS} =10V	--	80	--	nC
Q _{gs}	Gate-Source Charge		--	10	--	nC
Q _{gd}	Gate-Drain Charge		--	15.5	--	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =50V, I _D =4A, R _G =6.8Ω, V _{GS} =10V	--	23	--	nS
t _r	Turn-on Rise Time		--	112	--	nS
t _{d(off)}	Turn-Off Delay Time		--	50	--	nS
t _f	Turn-Off Fall Time		--	100	--	nS
Source- Drain Diode Characteristics @ T_c = 25°C (unless otherwise stated)						
V _{SD}	Forward on voltage	I _{SD} =20A, V _{GS} =0V	--	0.83	1.2	V
t _{rr}	Reverse Recovery Time	T _j =25°C, I _{sd} =4A, V _{GS} =0V	--	33	--	nS
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs		42		nC

NOTE:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.5mH, R_G = 25Ω, I_{AS} = 16A, V_{GS} = 10V. Part not recommended for use above this value
- ③ Pulse width ≤ 300μs; duty cycle ≤ 2%.

Typical Characteristics

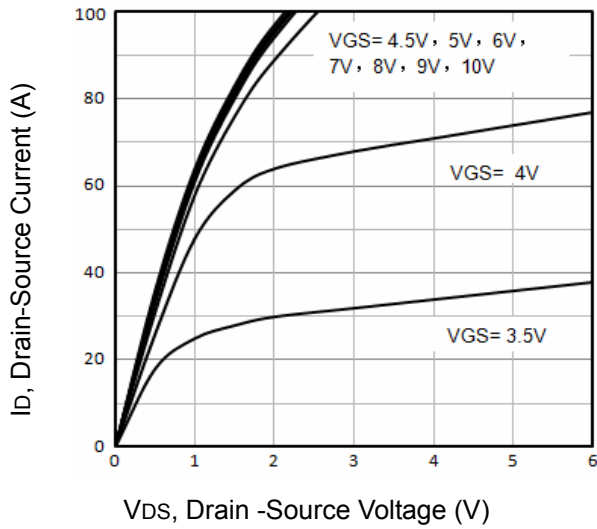


Fig1. Typical Output Characteristics

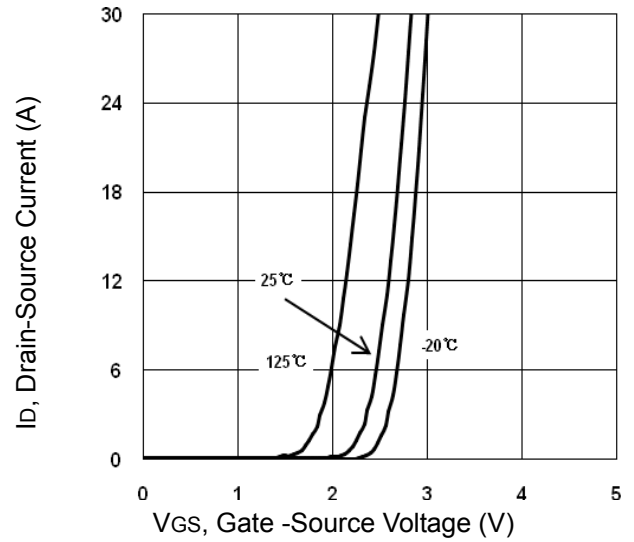


Fig2. Typical Transfer Characteristics

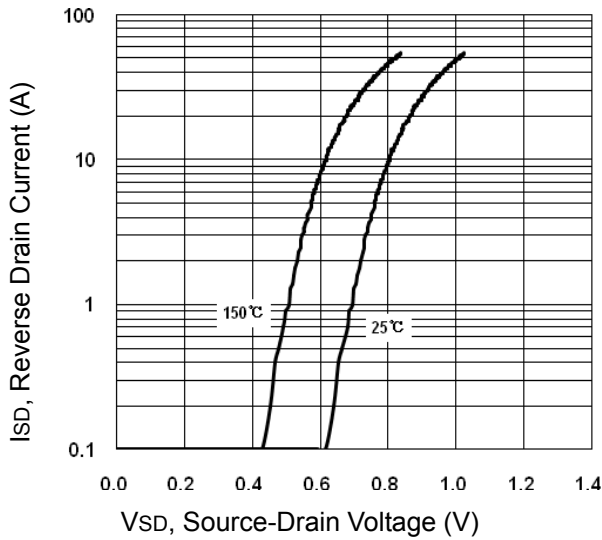


Fig3. Typical Source-Drain Diode Forward

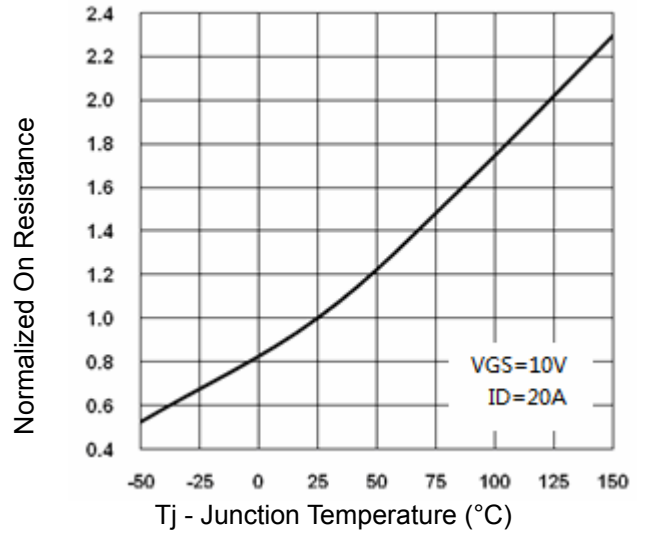


Fig4. Normalized On-Resistance Vs. Temperature

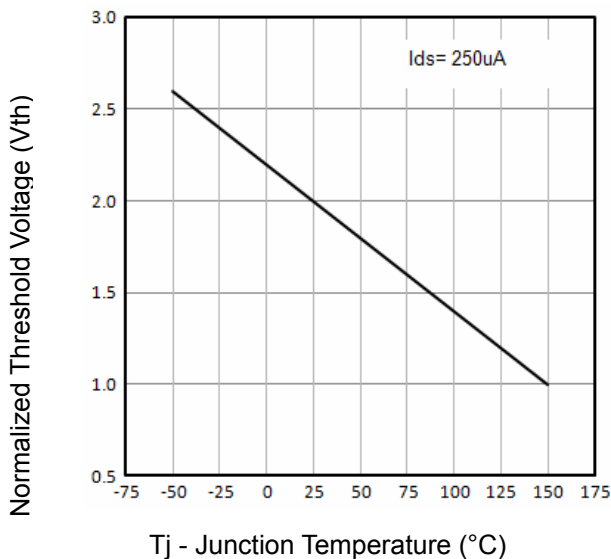


Fig5. Normalized Threshold Voltage Vs. Temperature

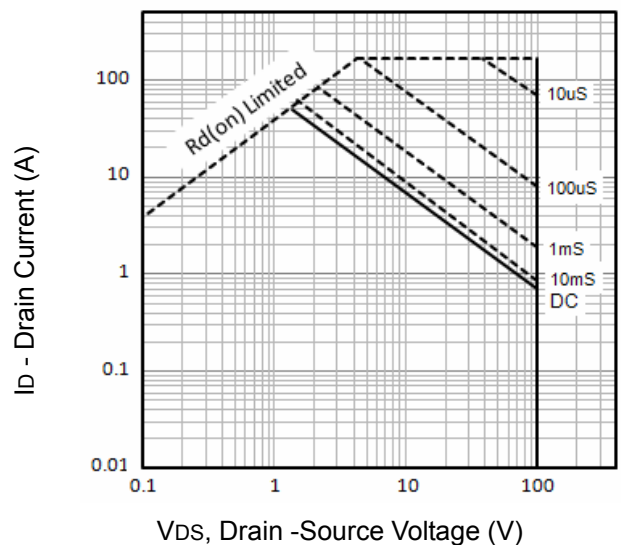


Fig6. Maximum Safe Operating Area

Typical Characteristics

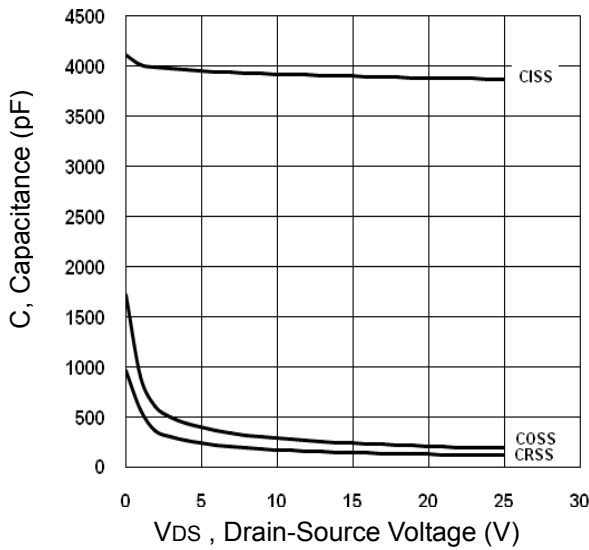


Fig7. Typical Capacitance Vs.Drain-Source Voltage

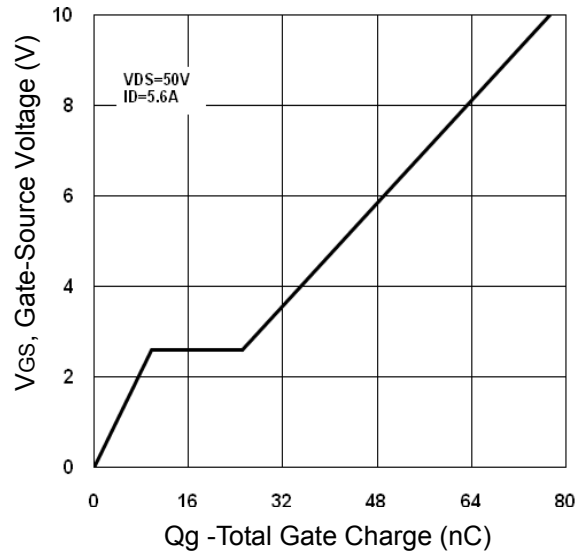


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

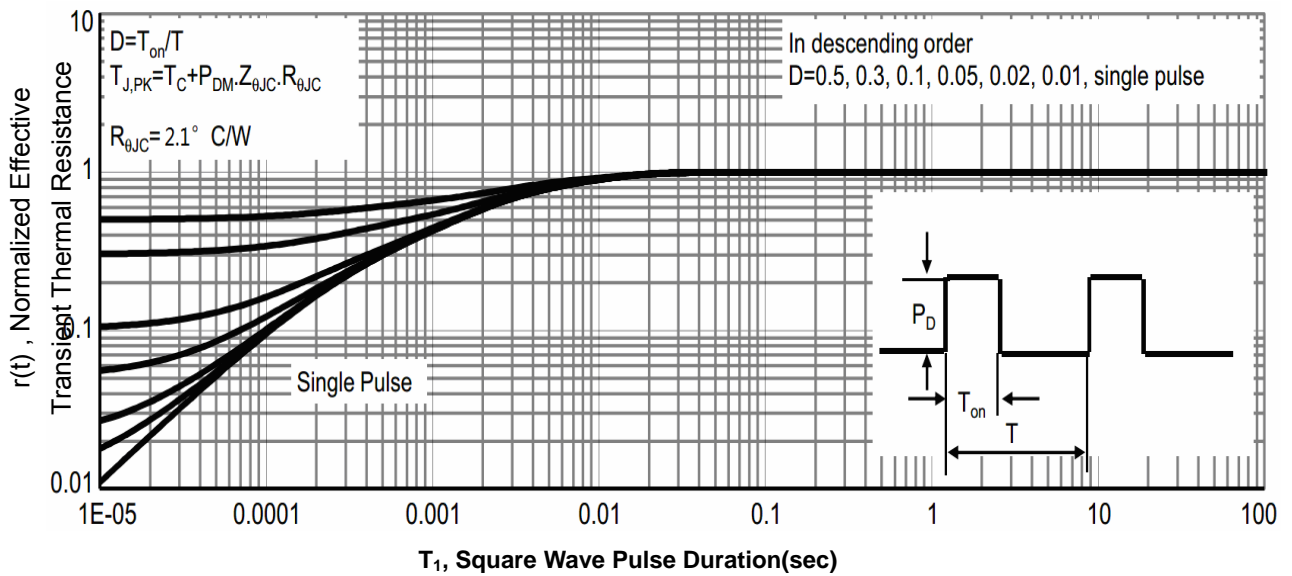


Fig9. T1 ,Transient Thermal Response Curve

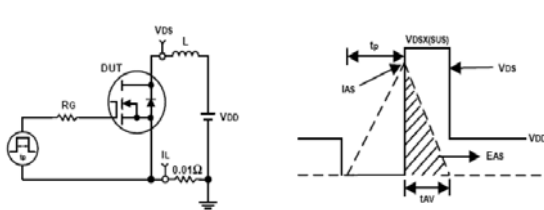


Fig10. Unclamped Inductive Test Circuit and waveforms

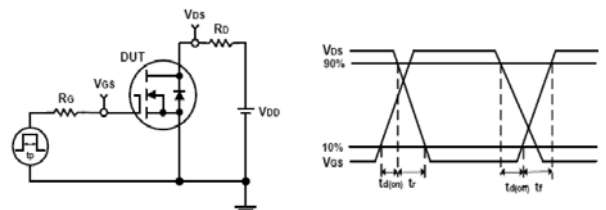
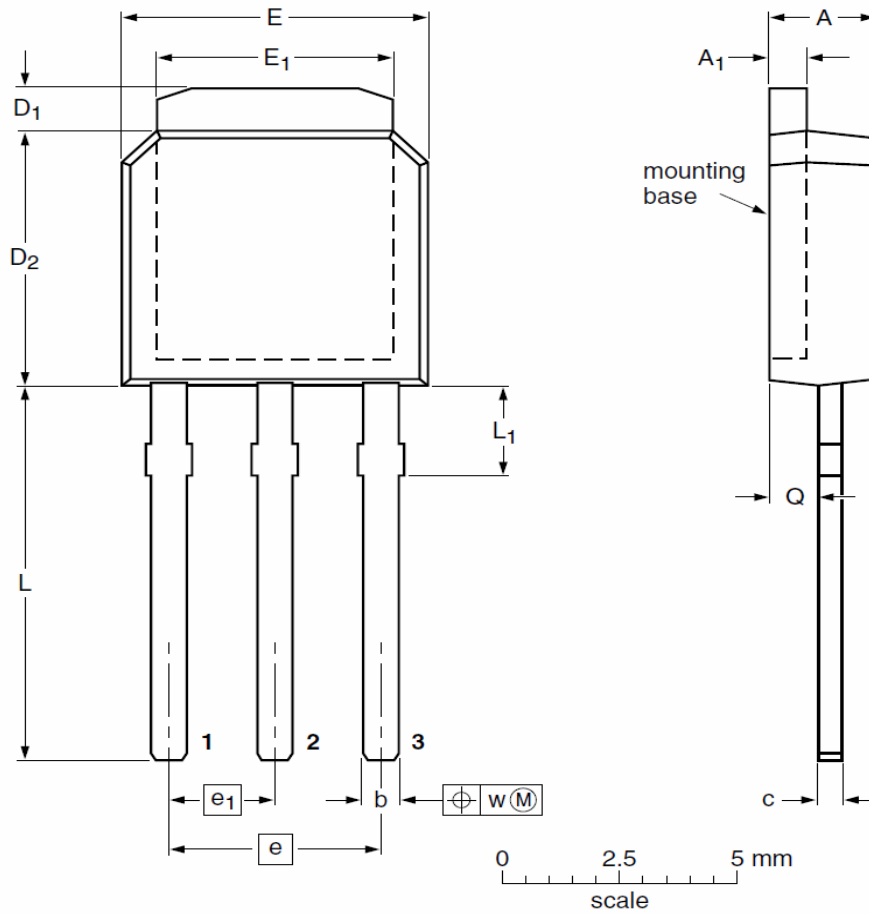


Fig11. Switching Time Test Circuit and waveforms

TO-251-L Package Outline



DIMENSIONS (unit : mm)

Label	Min	Typ	Max	Label	Min	Typ	Max
A	2.22	2.30	2.38	A ₁	0.46	0.55	0.93
b	0.71	0.78	0.89	c	0.46	0.51	0.56
D ₁	0.96	1.02	1.10	D ₂	5.98	6.05	6.22
E	6.47	6.60	6.73	E ₁	5.20	5.33	5.55
e	--	4.57	--	e ₁	--	2.28	--
L	9.20	9.38	9.60	L ₁	--	2.70	--
Q	1.00	1.05	1.10	w	--	0.30	--

Customer Service

Sales and Service:

sales@vgsemi.com

Vanguard Semiconductor CO., LTD

TEL: (86-755) -26902410

FAX: (86-755) -26907027

WEB: www.vgsemi.com